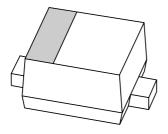
DISCRETE SEMICONDUCTORS

DATA SHEET



PMEG3002AEBLow V_F MEGA Schottky barrier diode

Product data sheet

2002 May 06



Low V_F MEGA Schottky barrier diode

PMEG3002AEB

FEATURES

Forward current: 0.2 AReverse voltage: 30 VVery low forward voltage

• Ultra small SMD package.

APPLICATIONS

Ultra high-speed switching

• High efficiency DC/DC conversion

· Voltage clamping

• Inverse-polarity protection

· Low voltage rectification

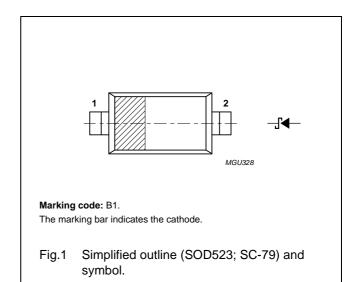
• Low power consumption applications.

DESCRIPTION

Planar Maximum Efficiency General Application (MEGA) Schottky barrier diode with an integrated guard ring for stress protection, encapsulated in a SOD523 (SC-79) ultra small SMD plastic package.

PINNING

PIN	DESCRIPTION
1	cathode
2	anode



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _R	continuous reverse voltage		_	30	V
I _F	continuous forward current		_	200	mA
I _{FRM}	repetitive peak forward current	$t_p \leq 1 \text{ s; } \delta \leq 0.5$	_	300	mA
I _{FSM}	non-repetitive peak forward current	t _p = 8.3 ms half sinewave; JEDEC method	_	1	A
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		_	125	°C
T _{amb}	operating ambient temperature		-65	+125	°C

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Low V_F MEGA Schottky barrier diode

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ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V _F	continuous forward voltage	see Fig.2			
		$I_F = 0.1 \text{ mA}$	130	190	mV
		I _F = 1 mA	190	250	mV
		I _F = 10 mA	255	300	mV
		I _F = 100 mA	355	400	mV
		I _F = 200 mA	420	480	mV
I _R	continuous reverse current	V _R = 10 V; see Fig.3; note 1	2.5	10	μΑ
C _d	diode capacitance	$V_R = 1 \text{ V}$; $f = 1 \text{ MHz}$; see Fig.4	20	25	pF

Note

1. Pulsed test: t_p = 300 μ s; δ = 0.02.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to	note 1	450	K/W
	ambient			

Note

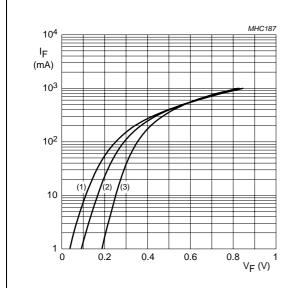
1. Refer to SOD523 (SC-79) standard mounting conditions.

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Low V_F MEGA Schottky barrier diode

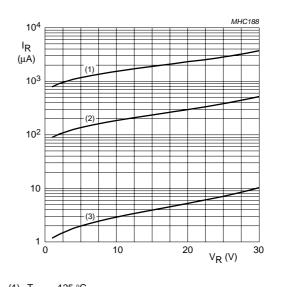
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GRAPHICAL DATA



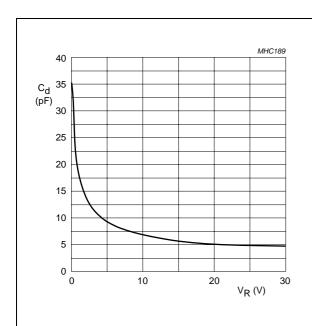
- (1) $T_{amb} = 125 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.2 Forward current as a function of forward voltage; typical values.



- (1) $T_{amb} = 125 \, ^{\circ}C$.
- (2) T_{amb} = 85 °C.
- (3) $T_{amb} = 25 \,^{\circ}C$.

Fig.3 Reverse current as a function of reverse voltage; typical values.



 $f = 1 \text{ MHz}; T_{amb} = 25 \,^{\circ}\text{C}.$

Fig.4 Diode capacitance as a function of reverse voltage; typical values.

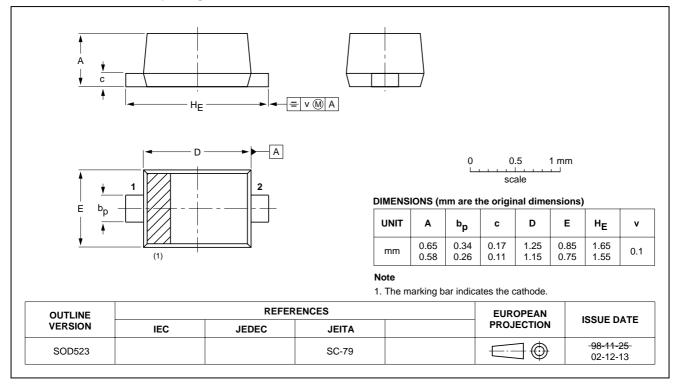
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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD523



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Low V_F MEGA Schottky barrier diode

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- The product status of device(s) described in this document may have changed since this document was published
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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com
For sales offices addresses send e-mail to: salesaddresses@nxp.com

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 Printed in The Netherlands
 613514/01/pp7
 Date of release: 2002 May 06
 Document order number: 9397 750 09622

